

Appl. No. 10/530,063; Docket No. BE02 0027 US
Amdt. dated February 14, 2006
Response to Office Action Dated February 6, 2006

Amendments to the Claims

1. (*Original*) A method of manufacturing a semiconductor device comprising the step of depositing an epitaxial layer based on Group IV elements on a silicon substrate by Chemical Vapor Deposition, and including employing nitrogen or a noble gas as a carrier gas.
2. (*Currently Amended*) A method as claimed in claim 1, which is employed to form the method forming an epitaxial layer based on at least one of the following: silicon, germanium, and carbon, ~~silicon, germanium and/or carbon~~.
3. (*Original*) A method as claimed in claim 2, wherein the epitaxial layer comprises $\text{Si}_{1-y}\text{C}_y$.
4. (*Original*) A method as claimed in claim 2, wherein the epitaxial layer comprises a SiGe epitaxial layer.
5. (*Original*) A method as claimed in claim 2, wherein the epitaxial layer comprises $\text{Si}_{1-x-y}\text{Ge}_x\text{C}_y$.
6. (*Original*) A method as claimed in claim 2, wherein the epitaxial layer comprises a silicon epitaxial layer.
7. (*Currently Amended*) A method as claimed in any one of the preceding claims, as claimed in claim 2, which is carried out at a low temperature.
8. (*Original*) A method as claimed in claim 7, which is carried out at a temperature of less than about 600°C.

Claims 9-16 (*Cancelled*).

17. (*New*) A method as claimed in claim 3, which is carried out at a low temperature.

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18. (New) A method as claimed in claim 4, which is carried out at a low temperature.

19. (New) A method as claimed in claim 5, which is carried out at a low temperature.

20. (New) A method as claimed in claim 6, which is carried out at a low temperature.